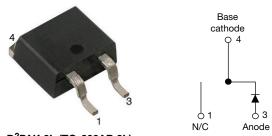
FREE

Hyperfast Rectifier, 30 A FRED Pt<sup>®</sup> G5



www.vishay.com

D<sup>2</sup>PAK 2L (TO-263AB 2L)

### LINKS TO ADDITIONAL RESOURCES

30	
3D Models	

SPICE Models Application Notes

PRIMARY CHARACTERISTICS								
I <sub>F(AV)</sub> 30 A								
V <sub>R</sub>	1200 V							
V <sub>F</sub> at I <sub>F</sub> at 125 °C	2.1 V							
t <sub>rr</sub>	26 ns							
T <sub>J</sub> max.	175 °C							
Package	D <sup>2</sup> PAK 2L (TO-263AB 2L)							
Circuit configuration	Single							

### **FEATURES**

- Hyperfast and optimized Q<sub>rr</sub>
- Best in class forward voltage drop and switching RoHS losses trade off COMPLIANT HALOGEN
- Optimized for high speed operation
- 175 °C maximum operating junction temperature
- Polyimide passivation
- Designed and qualified according JEDEC<sup>®</sup>-JESD 47
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

### **DESCRIPTION / APPLICATIONS**

Featuring a unique combination of low conduction and switching losses, this rectifier is the right choice for high frequency converters, both soft switched / resonant.

Specifically designed to improve efficiency of PFC and output rectification stages of EV / HEV battery charging stations, booster stage of solar inverters and UPS applications, these devices are perfectly matched to operate with MOSFETs or high speed IGBTs.

### **MECHANICAL DATA**

Case: D<sup>2</sup>PAK 2L (TO-263AB 2L)

Molding compound meets UL 94 V-0 flammability rating

Terminals: matte tin plated leads, solderable per J-STD-002

ABSOLUTE MAXIMUM RATINGS										
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS						
Repetitive peak reverse voltage	V <sub>RRM</sub>		1200	V						
Average rectified forward current	I <sub>F(AV)</sub>	T <sub>C</sub> = 83 °C, D = 0.50	30							
Non-repetitive peak surge current	I <sub>FSM</sub>	$T_{C}$ = 83 °C, $t_{p}$ = 10 ms, sine wave	190	А						
Repetitive peak forward current	I <sub>FRM</sub>	T <sub>C</sub> = 45 °C, D = 0.50, f = 20 kHz	60							
Operating junction and storage temperature	T <sub>J</sub> , T <sub>Stg</sub>		-55 to +175	°C						

<b>ELECTRICAL SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)										
PARAMETER         SYMBOL         TEST CONDITIONS         MIN.         TYP.         MAX.										
Breakdown voltage, blocking voltage	$V_{BR}, V_{R}$	I <sub>R</sub> = 100 μA	1200	-	-					
Forward voltage	M	I <sub>F</sub> = 30 A	-	2.6	3.3	V				
	V <sub>F</sub>	I <sub>F</sub> = 30 A, T <sub>J</sub> = 125 °C	-	2.1	-					
Povoroo lookogo ourront	I <sub>R</sub>	V <sub>R</sub> = V <sub>R</sub> rated	-	-	50					
Reverse leakage current		$T_J = 125 \text{ °C}, V_R = V_R \text{ rated}$	-	-	500	μA				
Junction capacitance	CT	V <sub>R</sub> = 200 V	-	17	-	pF				
Series inductance	L <sub>S</sub>	Measured to lead 5 mm from package body	-	8	-	nH				

Revision: 31-Jul-2023 1 For technical questions within your region: DiodesAmericas@vishay.com, DiodesAsia@vishay.com, DiodesEurope@vishay.com THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT www.vishav.com/doc?91000



www.vishay.com

# Vishay Semiconductors

<b>DYNAMIC RECOVERY CHARACTERISTICS</b> ( $T_J = 25$ °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST C	CONDITIONS	MIN.	TYP.	MAX.	UNITS		
		$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t$	$= 100 \text{ A/}\mu\text{s}, \text{V}_{\text{R}} = 30 \text{ V}$	-	26	-			
Reverse recovery time	t <sub>rr</sub>	T <sub>J</sub> = 25 °C		-	100	-	ns		
		T <sub>J</sub> = 125 °C		-	150	-			
Peak recovery current	1	T <sub>J</sub> = 25 °C	$I_F = 20 \text{ A}$	-	12	-	A nC		
	I <sub>RRM</sub>	T <sub>J</sub> = 125 °C	dI <sub>F</sub> /dt = 600 A/µs V <sub>R</sub> = 400 V	-	22	-			
Boueroo recourse obergo	0	T <sub>J</sub> = 25 °C		-	530	-			
Reverse recovery charge	Q <sub>rr</sub>	T <sub>J</sub> = 125 °C		-	1650	-			
Reverse recovery time	+	T <sub>J</sub> = 25 °C		-	80	-			
Reverse recovery lime	t <sub>rr</sub>	T <sub>J</sub> = 125 °C		-	120	-	ns		
Beek receiver aurrent		T <sub>J</sub> = 25 °C	I <sub>F</sub> = 30 A dI <sub>F</sub> /dt = 1000 A/µs	-	22	-	А		
Peak recovery current	IRRM	T <sub>J</sub> = 125 °C	$V_{\rm R} = 800 \text{ V}$	-	37	-	A		
Boueroo recourse obergo	0	T <sub>J</sub> = 25 °C	]	-	900	-	20		
Reverse recovery charge	Q <sub>rr</sub>	T <sub>J</sub> = 125 °C		-	2400	-	nC		

THERMAL - MECHANICAL SPECIFICATIONS									
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS			
Thermal resistance, junction-to-case	R <sub>thJC</sub>		-	-	1.1	°C/W			
Weight			-	2.0	-	g			
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)			
Maximum junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-55	-	175	°C			
Marking device		Case style D <sup>2</sup> PAK 2L (TO-263AB 2L)	E5TX3012S						



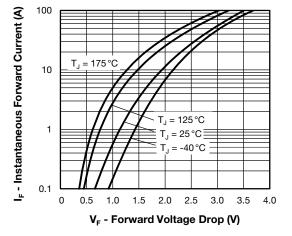


Fig. 1 - Typical Forward Voltage Drop Characteristics

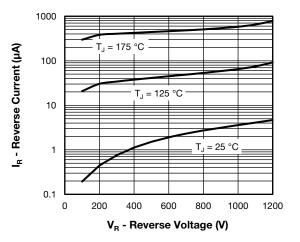


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

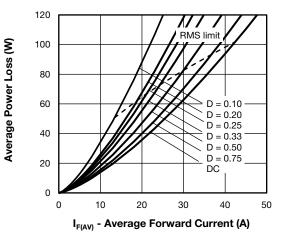


Fig. 5 - Typical Recovery Current vs. dl<sub>F</sub>/dt

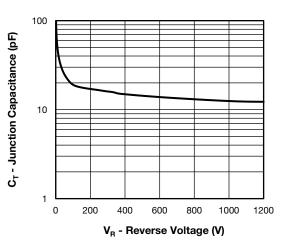


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

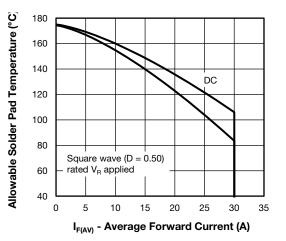


Fig. 4 - Maximum Allowable Case Temperature vs. Average Forward Current

 Revision: 31-Jul-2023
 3
 Document Number: 96999

 For technical questions within your region: DiodesAmericas@vishay.com, DiodesAsia@vishay.com, DiodesEurope@vishay.com
 THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT www.vishay.com/doc?91000

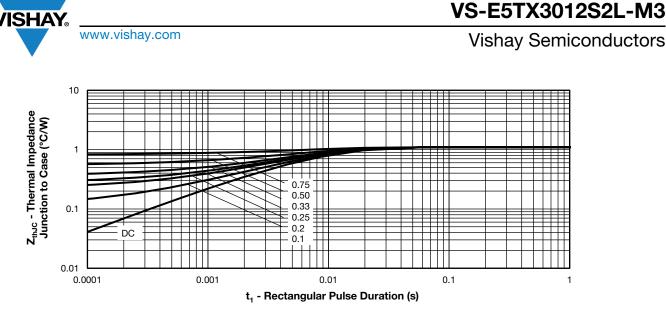


Fig. 6 - Thermal Impedance ZthJC Characteristics

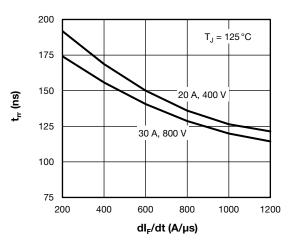
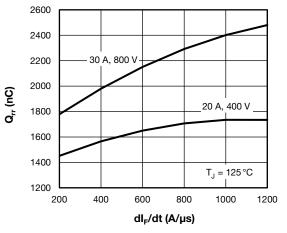
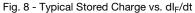


Fig. 7 - Typical Reverse Recovery Time vs. dI<sub>F</sub>/dt





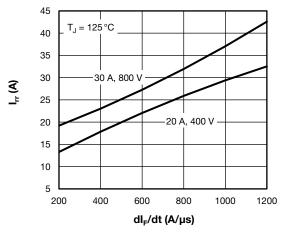


Fig. 9 - Typical Recovery Current vs. dI<sub>F</sub>/dt



# VS-E5TX3012S2L-M3

**Vishay Semiconductors** 

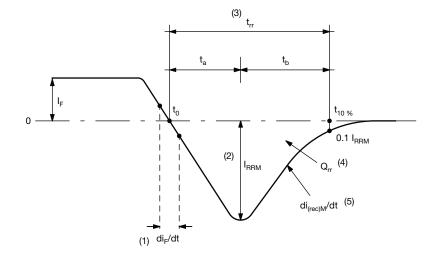


Fig. 10 - Reverse Recovery Waveform and Definitions

#### Notes

- (1) di<sub>F</sub>/dt rate of change of current through zero crossing
- <sup>(2)</sup> I<sub>RRM</sub> peak reverse recovery current
- <sup>(3)</sup>  $t_{rr}$  reverse recovery time measured from  $t_0$ , crossing point of negative going I<sub>F</sub>, to point  $t_{10\%}$ , 0.1 I<sub>RRM</sub>
- $^{(4)}~Q_{rr}$  area under curve defined by  $t_0$  and  $t_{10~\%}$

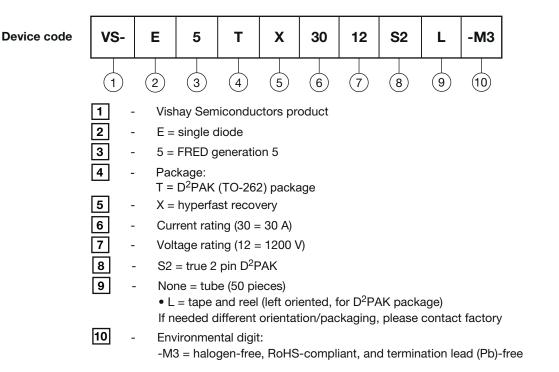
$$Q_{rr} = \int_{t_0}^{t_{10}\%} I(t)dt$$

 $^{(5)}$  di<sub>(rec)</sub>M/dt - peak rate of change of current during t<sub>b</sub> portion of t<sub>rr</sub>



**ORDERING INFORMATION TABLE** 

www.vishay.com



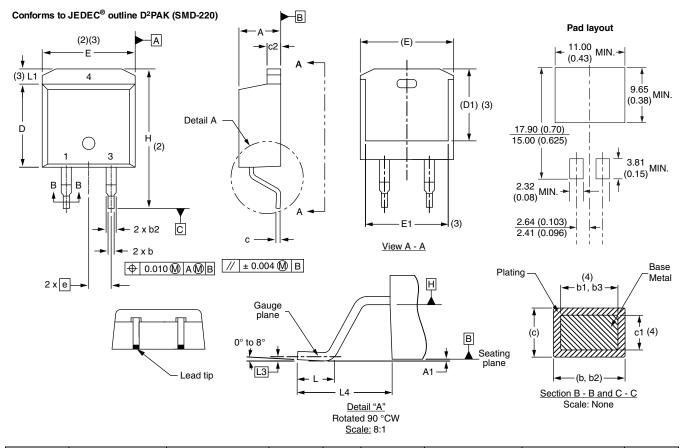
ORDERING INFORMATION (Example)							
PREFERRED P/N	BASE QUANTITY	PACKAGING DESCRIPTION					
VS-E5TX3012S2L-M3	800	13" diameter reel					

LINKS TO RELATED DOCUMENTS							
Dimensions	www.vishay.com/doc?96683						
Part marking information	www.vishay.com/doc?96693						
Packaging information	www.vishay.com/doc?95032						
SPICE model	www.vishay.com/doc?97017						



D<sup>2</sup>PAK 2L (TO-263AB 2L)

#### **DIMENSIONS** in millimeters and inches



SYMBOL	MILLIMETERS		INCHES		NOTES	TES	SYMBOL	MILLIM	IETERS	INC	HES	NOTES
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES	NOTES	STINDUL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.06	4.83	0.160	0.190			D1	6.86	8.00	0.270	0.315	3
A1	0.00	0.254	0.000	0.010			Е	9.65	10.67	0.380	0.420	2, 3
b	0.51	0.99	0.020	0.039			E1	7.90	8.80	0.311	0.346	3
b1	0.51	0.89	0.020	0.035	4		е	2.54	BSC	0.100	) BSC	
b2	1.14	1.78	0.045	0.070			Н	14.61	15.88	0.575	0.625	
b3	1.14	1.73	0.045	0.068	4		L	1.78	2.79	0.070	0.110	
с	0.38	0.74	0.015	0.029			L1	-	1.65	-	0.066	3
c1	0.38	0.58	0.015	0.023	4		L3	0.25 BSC		0.010	BSC	
c2	1.14	1.65	0.045	0.065			L4	4.78	5.28	0.188	0.208	
D	8.51	9.65	0.335	0.380	2							

#### Notes

<sup>(1)</sup> Dimensioning and tolerancing per ASME Y14.5 M-1994

(2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
 (3) Thermal and contain antional within dimension E 1.1, D1 and E1.

<sup>(3)</sup> Thermal pad contour optional within dimension E, L1, D1 and E1

<sup>(4)</sup> Dimension b1 and c1 apply to base metal only

<sup>(5)</sup> Datum A and B to be determined at datum plane H

<sup>(6)</sup> Controlling dimension: inch

(7) Outline conforms to JEDEC® outline TO-263AB

Revision: 14-Mar-2022

1

For technical questions within your region: <u>DiodesAmericas@vishay.com</u>, <u>DiodesAsia@vishay.com</u>, <u>DiodesEurope@vishay.com</u> THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT <u>www.vishay.com/doc?91000</u>



Vishay

# Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Hyperlinks included in this datasheet may direct users to third-party websites. These links are provided as a convenience and for informational purposes only. Inclusion of these hyperlinks does not constitute an endorsement or an approval by Vishay of any of the products, services or opinions of the corporation, organization or individual associated with the third-party website. Vishay disclaims any and all liability and bears no responsibility for the accuracy, legality or content of the third-party website or for that of subsequent links.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.

© 2024 VISHAY INTERTECHNOLOGY, INC. ALL RIGHTS RESERVED

Revision: 01-Jan-2024